HD31935
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB GaAs linear design
Instantaneous ultra-wide Bandwidth
Suitable for all single channel modulation standards
Built-in protection circuits
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	2.0 - 20.0GHz	
Power Output Psat	1 Watt Min	CW / 18 - 20GHz 29dBm
Power Output P1dB GCP	0.5 Watt Min	CW
Small Signal Gain	30 dB Min	
Power Gain Flatness	4 dB p-p Max	
Input Return Loss	-10 dB Typ	
Harmonics	-20 dBc Typ	At rated Pout
Noise Figure	6 dB Max	
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	12 VDC ±0.2V	
Current Consumption	1.2 Amp Max	At rated Pout
Input Power Protection	+8 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +70 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	70 x 60x 15 mm	Excluding connectors
Weight	300 gr.	
RF Connectors In/Out	Hi-Freq. SMA female	
DC Power	Feed Thru	
Cooling	External Heatsink	Forced air required

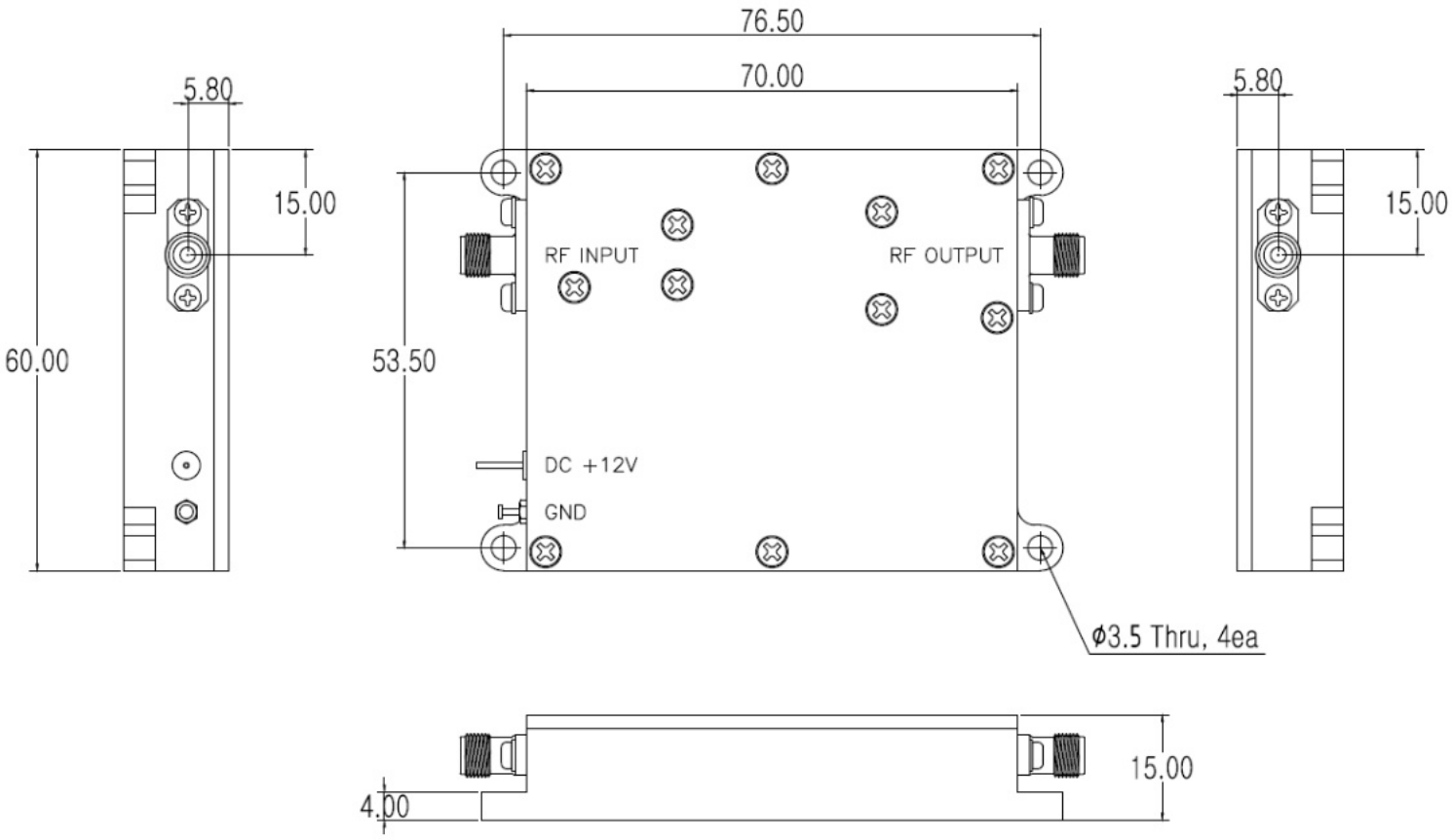
PIN ASSIGNMENT

Pin	Function	Description
1	DC Voltage	+12VDC
2	GND	GND

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Specifications subject to change without notice. Specifications and drawings m r vary with selected options.

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OUTLINE DRAWING



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